

Dimension



156 mm x 156 mm \pm 0.5 mm

Wafer Thickness:



200 μ m \pm 20 μ m.

Front side (–)

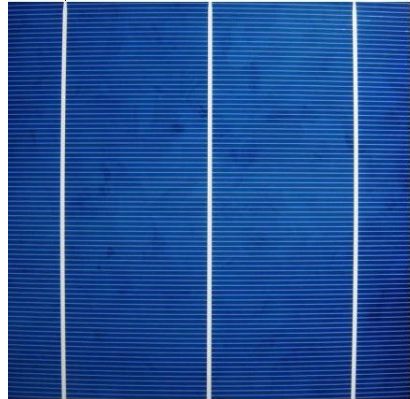


- Three 1.5 mm wide bus bars(silver)
- Distance 52 mm, acid textured surface,
- with blue silicon nitride anti-reflection coating.

Back side (+)



- 2.3 mm wide silver continuous bus bars,
- aluminum back surface field



Typical Electrical Characteristics

P/N	Eff.(%)	Minimum Power	Impp	Vmpp	Isc	Voc
UT6M-180	18.00 – 18.20	4.38	8.135	0.540	8.649	0.638
UT6M-178	17.80 – 18.00	4.33	8.107	0.537	8.625	0.637
UT6M-176	17.60 – 17.80	4.28	8.068	0.535	8.586	0.635
UT6M-174	17.40 – 17.60	4.23	8.024	0.531	8.544	0.632
UT6M-172	17.20 – 17.40	4.19	7.978	0.528	8.498	0.630
UT6M-170	17.00 – 17.20	4.14	7.922	0.526	8.443	0.628
UT6M-168	16.80 – 17.00	4.09	7.869	0.523	8.380	0.624
UT6M-166	16.60 – 16.80	4.04	7.804	0.522	8.313	0.622
UT6M-164	16.40 – 16.60	3.99	7.723	0.522	8.235	0.623
UT6M-162	16.20 – 16.40	3.94	7.654	0.517	8.196	0.620
UT6M-160	16.00 – 16.20	3.89	7.625	0.513	8.172	0.616

Typical Temperature Coefficients

Current (Alpha) : +2.47 mA/K

Voltage (Beta) : - 2.02 mV/K

Power (Gamma) : - 0.39 %/K